PRELIMINARY SPECIFICATION

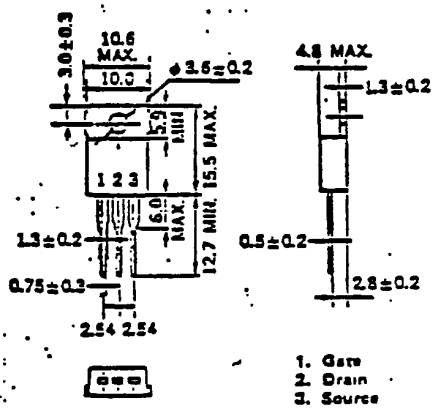
NEC
ELECTRON DEVICE

MOS FIELD EFFECT TRANSISTOR

2SK855

FAST SWITCHING N-CHANNEL SILICON POWER MOS FET

PACKAGE DIMENSIONS
(Unit: mm)



Features

Suitable for switching power supplies, actuator controls and pulse circuits
Low RDS(on)

Absolute Maximum Ratings(Ta=25°C)

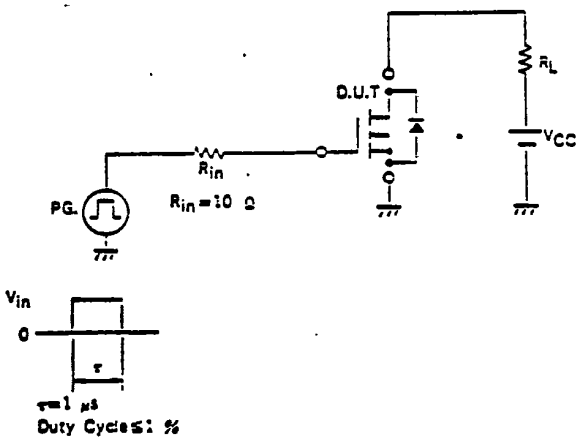
Drain to Source Voltage	VDSS	500V
Gate to Source Voltage	VGSS	± 20V
Continuous Drain Curre	ID(DC)	± 5A
Pulse Drain Current	ID(pulse)	*± 20A
Total Power Dissipation	PT	1.5W
Total Power Dissipation	PT**	50W
Channel Temperature	Tch	150 °C
Storage Temperature	Tstg	-55to+150 °C

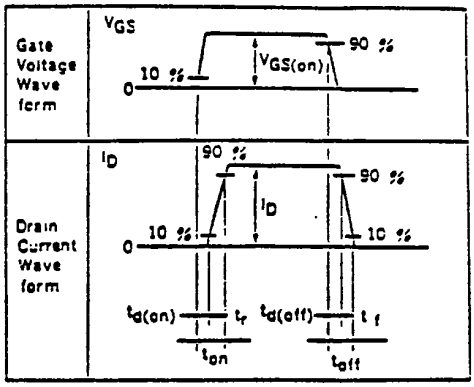
* PW ≦100 us, Duty Cycle≦2%
** Tc=25 °C

Electrical Characteristics (Ta=25 °C)

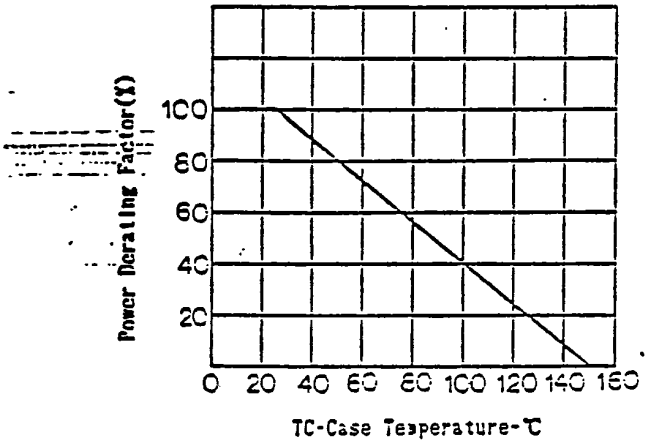
Characteristics	Symbol	Min.	Typ.	Max.	Unit	Test Conditions
Drain Leakage Current	IDSS			100	μA	VDS=500V,VGS=0
Gate to Source Leakage Current	IGSS			±100	nA	VGS=±20V,VDS=0
Gate to Source Cutoff Voltage	VGS(off)	1.5		3.5	V	VDS=10V,ID=1.0mA
Forward Transfer Admittance	yfs	2.5			S	VDS=10V,ID=2.5A
Drain to Source On-State Resistance	RDS(on)			1.5	Ω	VGS=10V,ID=2.5A
Resistance						
Input Capacitance	Ciss		700		pF	VDS= 10V,
Output Capacitance	Coss		175		pF	VGS=0,
Reverse Transfer Capacitance	Crss		40		pF	f=1.0MHz
Turn-On Delay Time	td(on)		10		ns	ID=2.5A.
Rise Time	tr		15		ns	VGS(on)= 10V,
Turn-Off Delay Time	td(off)		40		ns	Vcc=150V.
Fall Time	tf		15		ns	RL= 60 Ω

TURN-ON AND TURN-OFF TIME TEST CIRCUIT

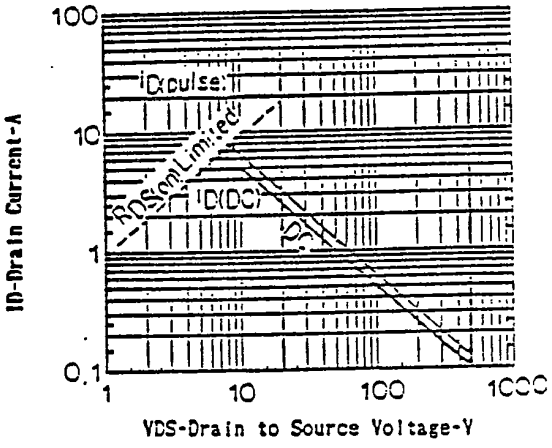




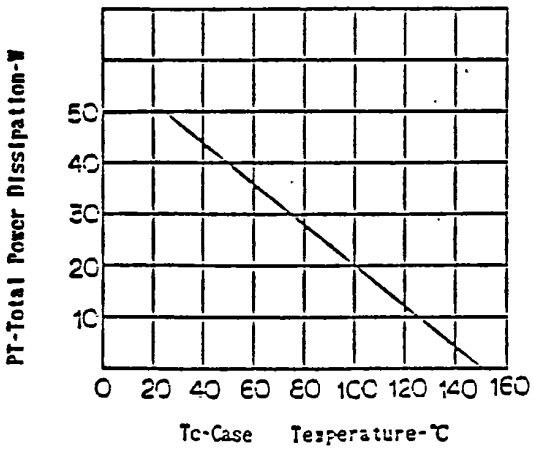
DERATING FACTOR OF FORWARD BIAS SAFE OPERATING AREA



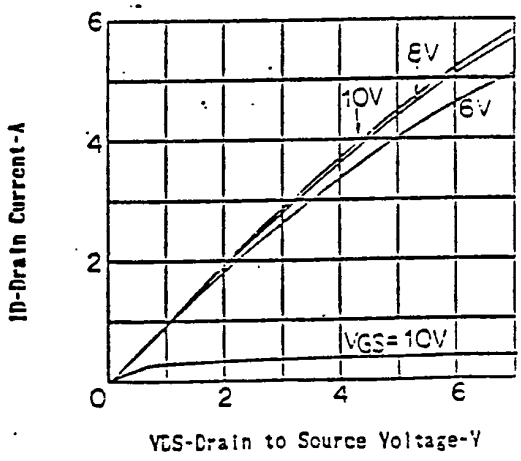
FORWARD BIAS SAFE OPERATING AREA



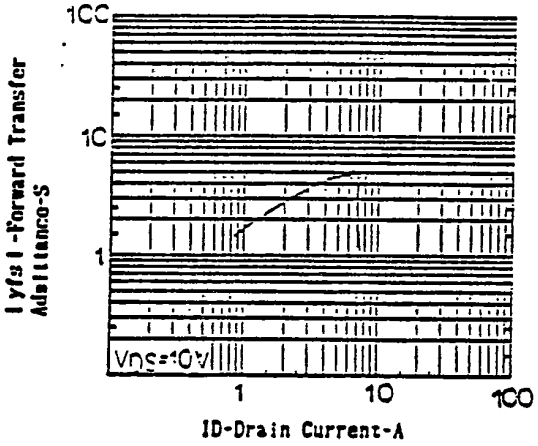
TOTAL POWER DISSIPATION vs. CASE TEMPERATURE



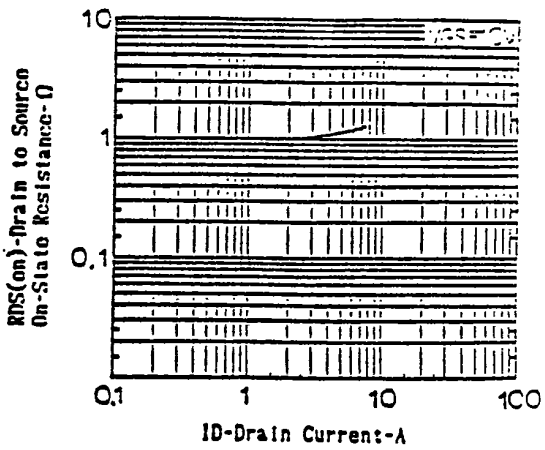
DRAIN CURRENT vs. DRAIN TO SOURCE VOLTAGE



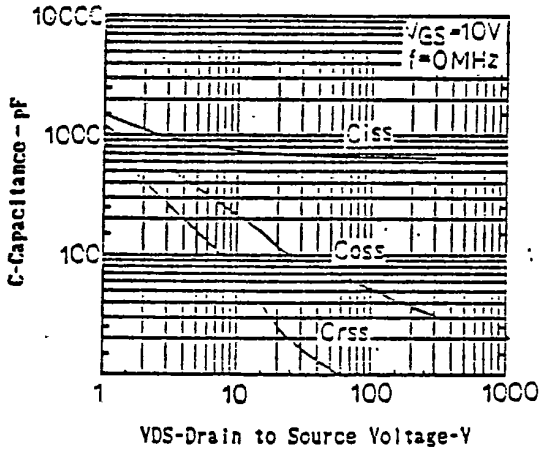
FORWARD TRANSFER ADMITTANCE vs. DRAIN CURRENT



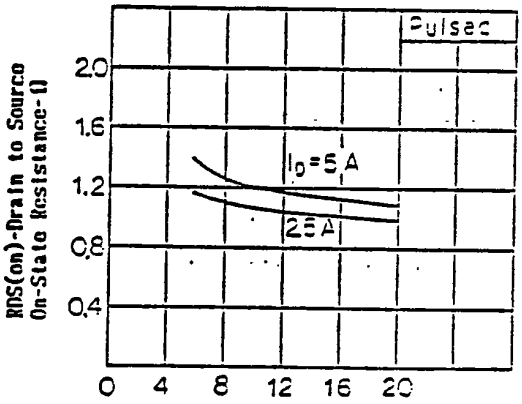
DRAIN TO SOURCE ON-STATE RESISTANCE vs. DRAIN CURRENT



CAPACITANCE vs. DRAIN TO SOURCE VOLTAGE



DRAIN TO SOURCE ON-STATE RESISTANCE vs. GATE TO SOURCE VOLTAGE



TURN-ON AND TURN-OFF TIME